

PMF250XNE **30V N-channel Trench MOSFET**

Product data sheet

1. **General description**

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. **Features and benefits**

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	1	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.9 \text{ A}; T_j = 25 \text{ °C}$		-	212	254	mΩ

^[1] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



30V N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	□ 3	D I
2	S	source		
3	D	drain	1 2 SC-70 (SOT323)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF250XNE	SC-70	plastic surface-mounted package; 3 leads	SOT323			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF250XNE	Z%W

[1] % = placeholder for manufacturing site code

30V N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	1	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.9	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	275	mW
			[1]	-	342	mW
		T _{sp} = 25 °C		-	1.1	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode		ı	-	1	
I _S	source current	T _{amb} = 25 °C	[1]	-	0.3	Α

^[1] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

30V N-channel Trench MOSFET

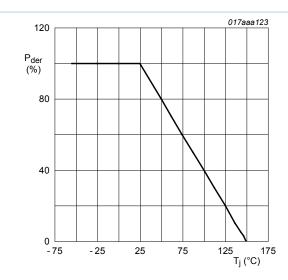


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

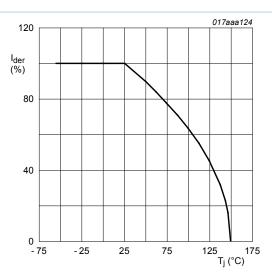


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

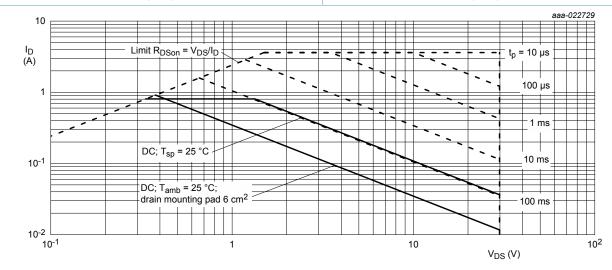


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	397	457	K/W
	from junction to ambient		[2]	-	318	366	K/W
		t ≤ 5 s	[2]	-	256	294	K/W

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30V N-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	102	117	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

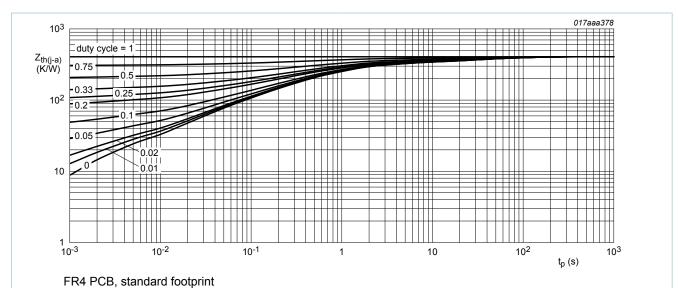
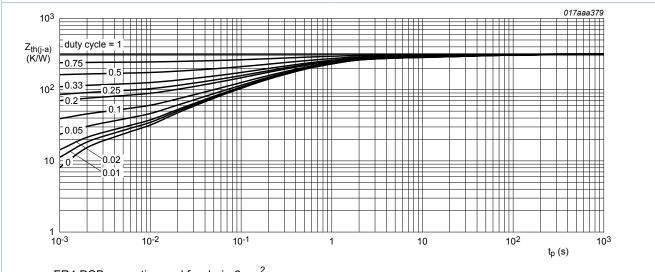


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30V N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		_
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	0.75	1	1.25	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
R _{DSon} drain-source on-state resistance		V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 25 °C	-	212	254	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 150 °C	-	346	416	mΩ
	V _{GS} = 2.5 V; I _D = 0.8 A; T _j = 25 °C	-	269	321	mΩ	
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 0.9 A; T_{j} = 25 °C	-	3.5	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V;	-	1.05	1.65	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.27	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	81	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	13	-	pF
C _{rss}	reverse transfer capacitance		-	8.5	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	6	-	ns
Source-dra	in diode	1		'		
V_{SD}	source-drain voltage	$I_S = 0.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
		4		_	_	

30V N-channel Trench MOSFET

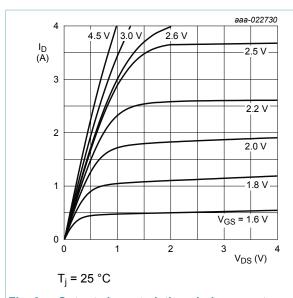


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

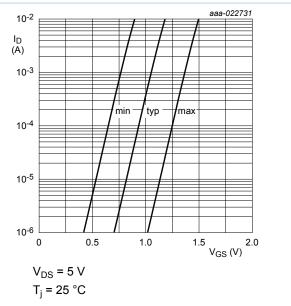


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

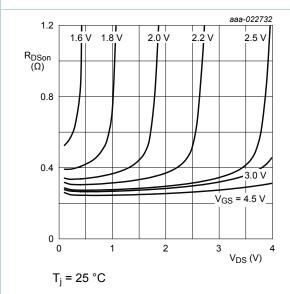


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

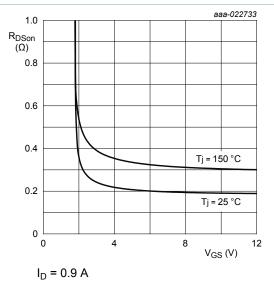


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30V N-channel Trench MOSFET

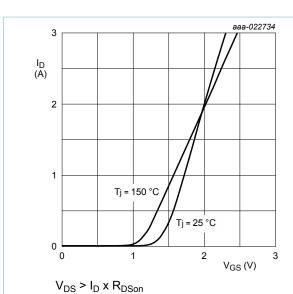


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

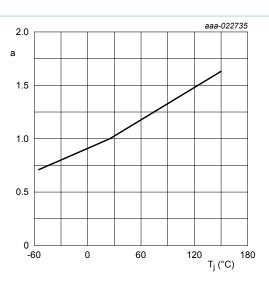


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

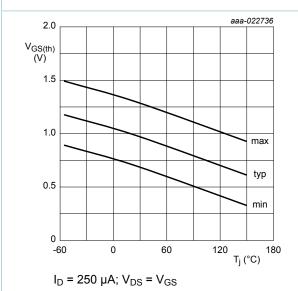


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

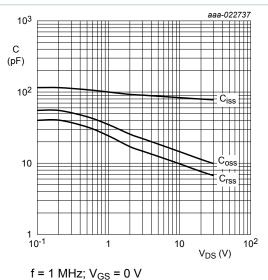


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

8 / 15

30V N-channel Trench MOSFET

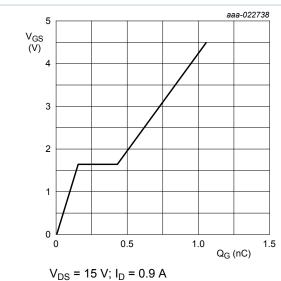


Fig. 14. Gate-source voltage as a function of gate charge; typical values

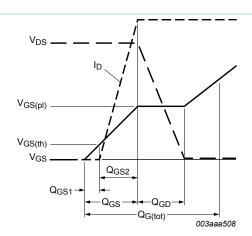


Fig. 15. Gate charge waveform definitions

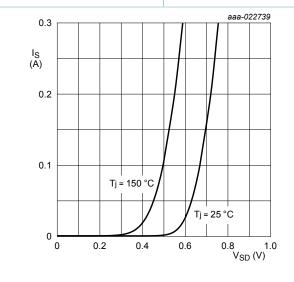
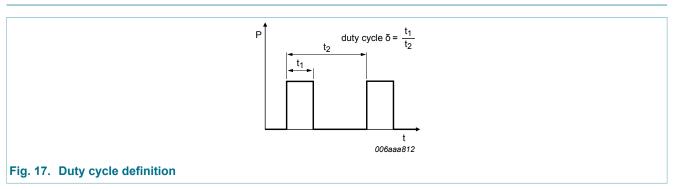


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



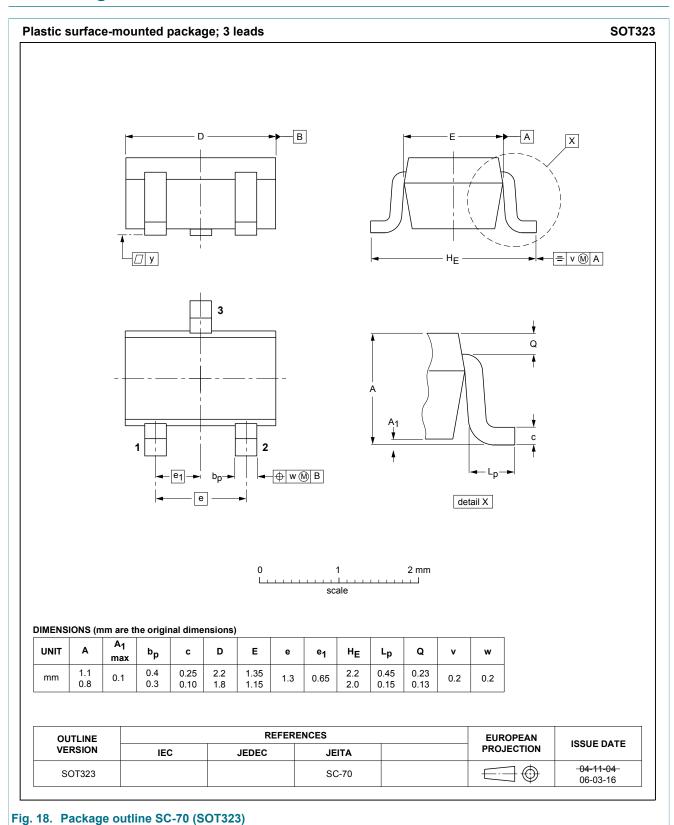
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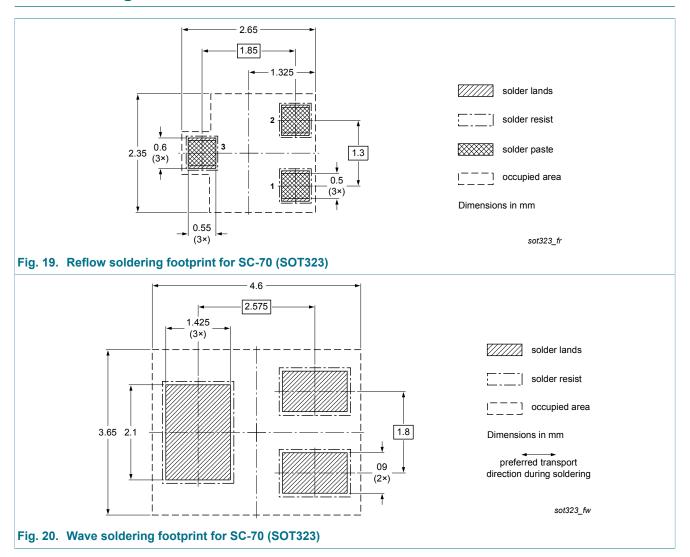
30V N-channel Trench MOSFET

12. Package outline



30V N-channel Trench MOSFET

13. Soldering



30V N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF250XNE v.1	20160428	Product data sheet	-	-

30V N-channel Trench MOSFET

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30V N-channel Trench MOSFET

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14 / 15

30V N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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15 / 15

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